

Silicon PNP Power Transistors

2SA1262

DESCRIPTION

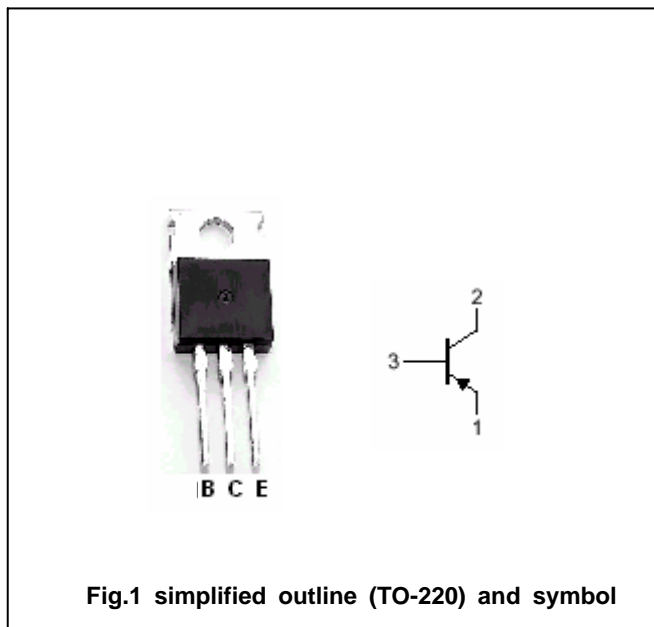
- With TO-220 package
- Complement to type 2SC3179

APPLICATIONS

- Audio and general purpose

PINNING

| PIN | DESCRIPTION |
|-----|--------------------------------------|
| 1 | Emitter |
| 2 | Collector;connected to mounting base |
| 3 | Base |



Absolute maximum ratings(Ta=25)

| SYMBOL | PARAMETER | CONDITIONS | VALUE | UNIT |
|------------------|-----------------------------|--------------------|---------|------|
| V _{CBO} | Collector-base voltage | Open emitter | -60 | V |
| V _{CEO} | Collector-emitter voltage | Open base | -60 | V |
| V _{EBO} | Emitter-base voltage | Open collector | -6 | V |
| I _C | Collector current | | -4 | A |
| I _B | Base current | | -1 | A |
| P _C | Collector power dissipation | T _C =25 | 30 | W |
| T _j | Junction temperature | | 150 | |
| T _{stg} | Storage temperature | | -55~150 | |

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CHARACTERISTICS

T_j=25 unless otherwise specified

| SYMBOL | PARAMETER | CONDITIONS | MIN | TYP. | MAX | UNIT |
|----------------------|--------------------------------------|--|-----|------|------|------|
| V _{(BR)CEO} | Collector-emitter breakdown voltage | I _C =-25mA, I _B =0 | -60 | | | V |
| V _{CEsat} | Collector-emitter saturation voltage | I _C =-2A; I _B =-0.2A | | | -0.6 | V |
| I _{CBO} | Collector cut-off current | V _{CB} =-60V; I _E =0 | | | -100 | μA |
| I _{EBO} | Emitter cut-off current | V _{EB} =-6V; I _C =0 | | | -100 | μA |
| h _{FE} | DC current gain | I _C =-1A; V _{CE} =-4V | 40 | | | |
| f _T | Transition frequency | I _E =0.2A; V _{CE} =-12V | | 15 | | MHz |
| C _{ob} | Output capacitance | I _E =0; V _{CB} =-10V; f=1MHz | | 90 | | pF |

Switching times

| | | | | | | |
|-----------------|--------------|---|--|------|--|----|
| t _{on} | Turn-on time | I _C =-2A; I _{B1} =-I _{B2} =-0.2A R _L =10Ω; V _{CC} =-20V | | 0.25 | | μs |
| t _s | Storage time | | | 0.75 | | μs |
| t _f | Fall time | | | 0.25 | | μs |

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PACKAGE OUTLINE

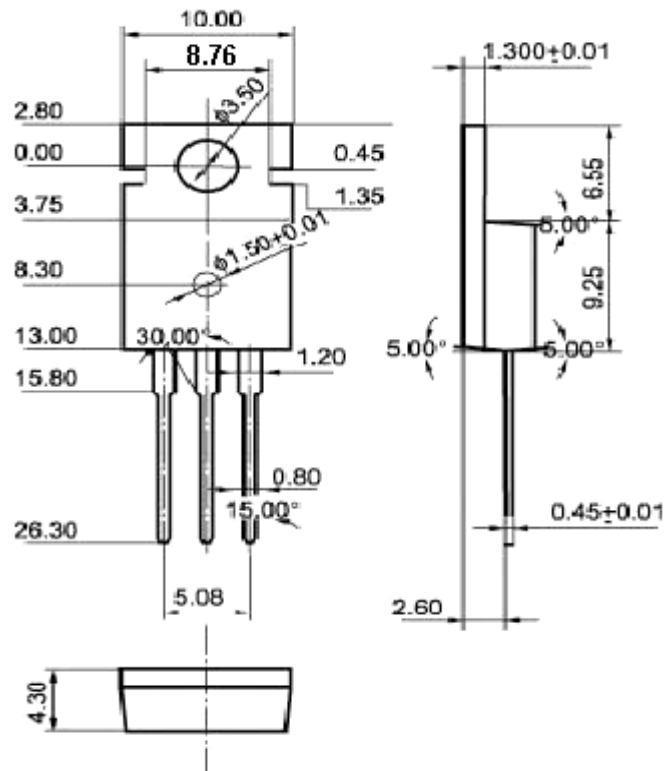


Fig.2 Outline dimensions(unindicated tolerance: ± 0.10 mm)

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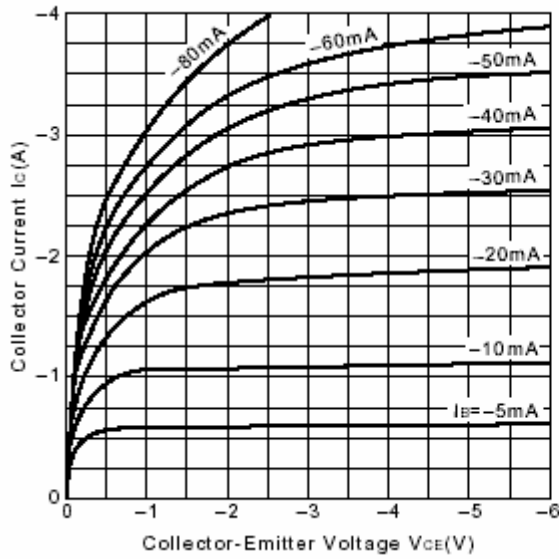


Fig.3 Static Characteristic

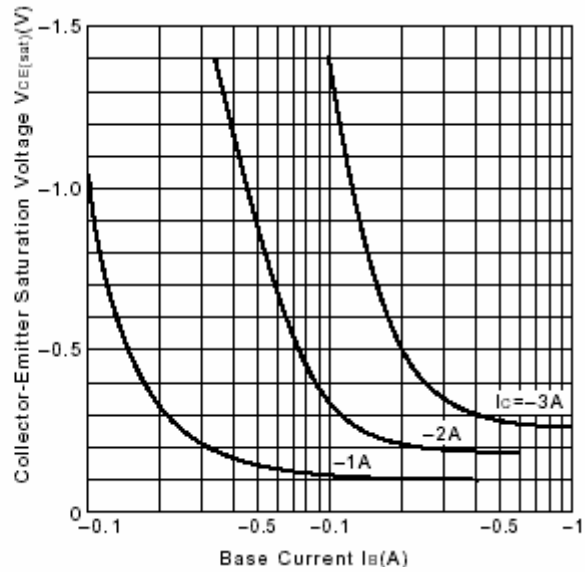


Fig.4 $V_{CE(sat)}-I_B$ Characteristics

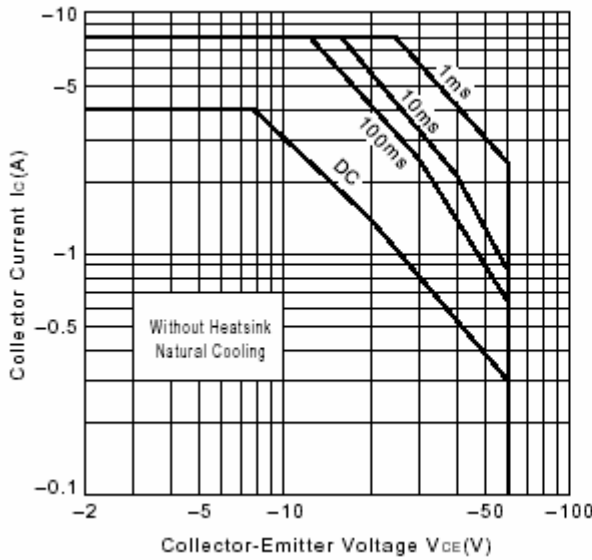


Fig.5 Safe Operating Area

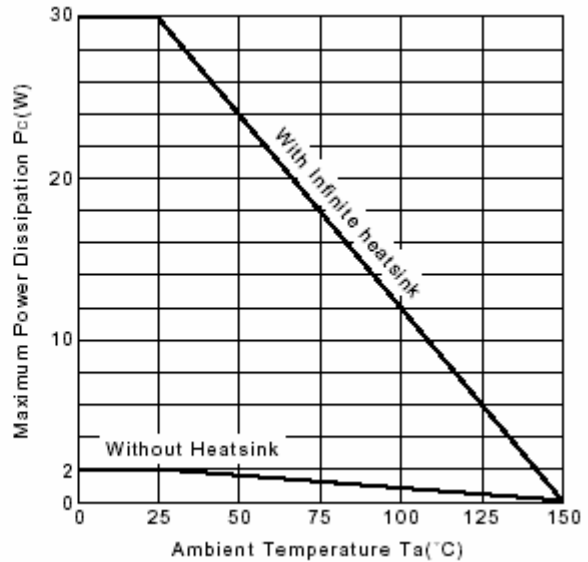


Fig.6 P_c-T_a Derating

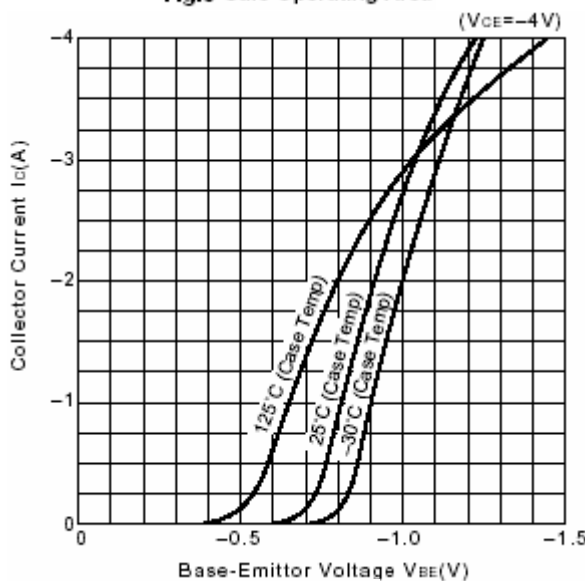


Fig.7 I_C-V_{BE}

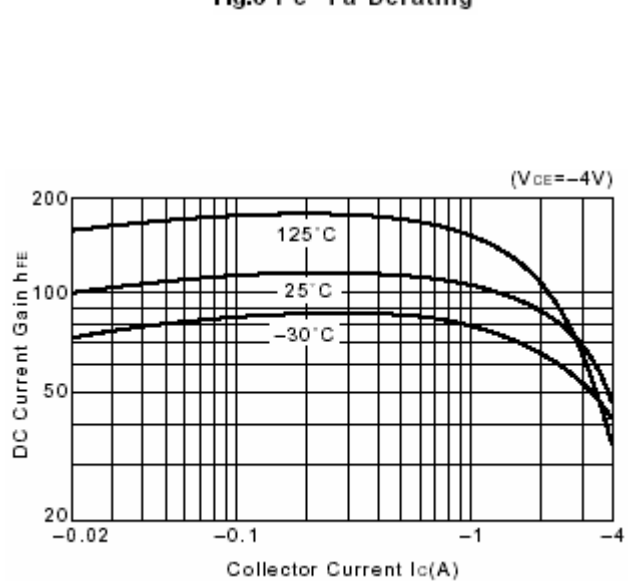


Fig.8 DC current Gain